Electronic Transport in Graphene on hexagonal Boron Nitride Devices

Pablo Jarillo-Herrero

MIT, 77 Massachusetts Avenue Cambridge (USA)

Hexagonal boron nitride (hBN) has been recently shown to be a high quality substrate for graphene devices. In this talk I will review our recent experiments on graphene on hBN devices. In particular I will describe STM measurements that show that electron-hole puddles are much reduced for graphene on hBN compared to graphene on SiO2, and also our experiments on quantum Hall effect and Landau level crossings of Dirac fermions on high mobility trilayer graphene on hBN.